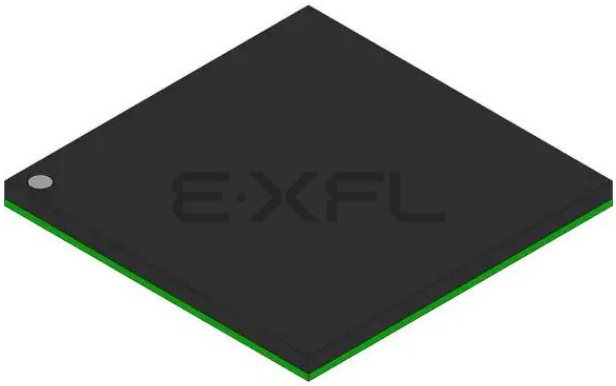

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	382
Number of Gates	526000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=ep20k200fc484-3n

Table 8. Comparison of APEX 20K & APEX 20KE Features

Feature	APEX 20K Devices	APEX 20KE Devices
MultiCore system integration	Full support	Full support
SignalTap logic analysis	Full support	Full support
32/64-Bit, 33-MHz PCI	Full compliance in -1, -2 speed grades	Full compliance in -1, -2 speed grades
32/64-Bit, 66-MHz PCI	-	Full compliance in -1 speed grade
MultiVolt I/O	2.5-V or 3.3-V V_{CCIO} V_{CCIO} selected for device Certain devices are 5.0-V tolerant	1.8-V, 2.5-V, or 3.3-V V_{CCIO} V_{CCIO} selected block-by-block 5.0-V tolerant with use of external resistor
ClockLock support	Clock delay reduction 2× and 4× clock multiplication	Clock delay reduction $m/(n \times v)$ or $m/(n \times k)$ clock multiplication Drive ClockLock output off-chip External clock feedback ClockShift LVDS support Up to four PLLs ClockShift, clock phase adjustment
Dedicated clock and input pins	Six	Eight
I/O standard support	2.5-V, 3.3-V, 5.0-V I/O 3.3-V PCI Low-voltage complementary metal-oxide semiconductor (LVCMOS) Low-voltage transistor-to-transistor logic (LVTTL)	1.8-V, 2.5-V, 3.3-V, 5.0-V I/O 2.5-V I/O 3.3-V PCI and PCI-X 3.3-V Advanced Graphics Port (AGP) Center tap terminated (CTT) GTL+ LVCMOS LVTTL True-LVDS and LVPECL data pins (in EP20K300E and larger devices) LVDS and LVPECL signaling (in all BGA and FineLine BGA devices) LVDS and LVPECL data pins up to 156 Mbps (in -1 speed grade devices) HSTL Class I PCI-X SSTL-2 Class I and II SSTL-3 Class I and II
Memory support	Dual-port RAM FIFO RAM ROM	CAM Dual-port RAM FIFO RAM ROM

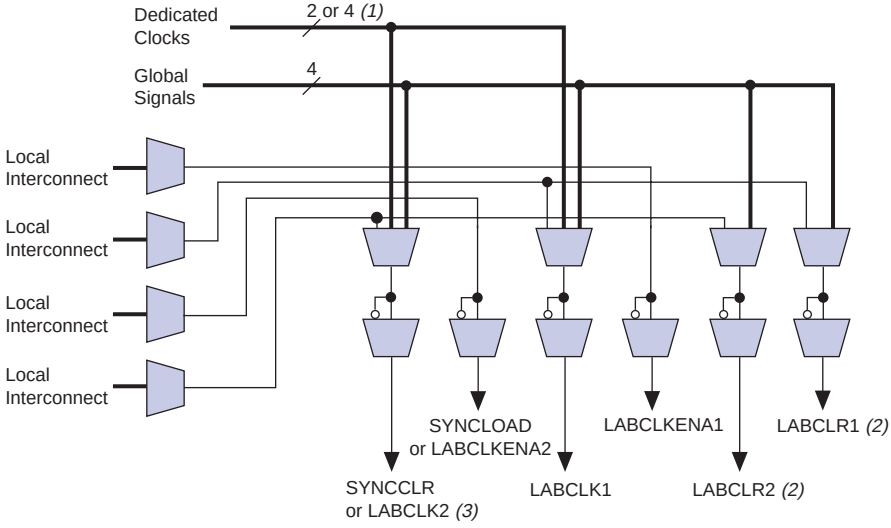
Each LAB contains dedicated logic for driving control signals to its LEs and ESBs. The control signals include clock, clock enable, asynchronous clear, asynchronous preset, asynchronous load, synchronous clear, and synchronous load signals. A maximum of six control signals can be used at a time. Although synchronous load and clear signals are generally used when implementing counters, they can also be used with other functions.

Each LAB can use two clocks and two clock enable signals. Each LAB's clock and clock enable signals are linked (e.g., any LE in a particular LAB using `CLK1` will also use `CLKENA1`). LEs with the same clock but different clock enable signals either use both clock signals in one LAB or are placed into separate LABs.

If both the rising and falling edges of a clock are used in a LAB, both LAB-wide clock signals are used.

The LAB-wide control signals can be generated from the LAB local interconnect, global signals, and dedicated clock pins. The inherent low skew of the FastTrack Interconnect enables it to be used for clock distribution. Figure 4 shows the LAB control signal generation circuit.

Figure 4. LAB Control Signal Generation



Notes to Figure 4:

(1) APEX 20KE devices have four dedicated clocks.

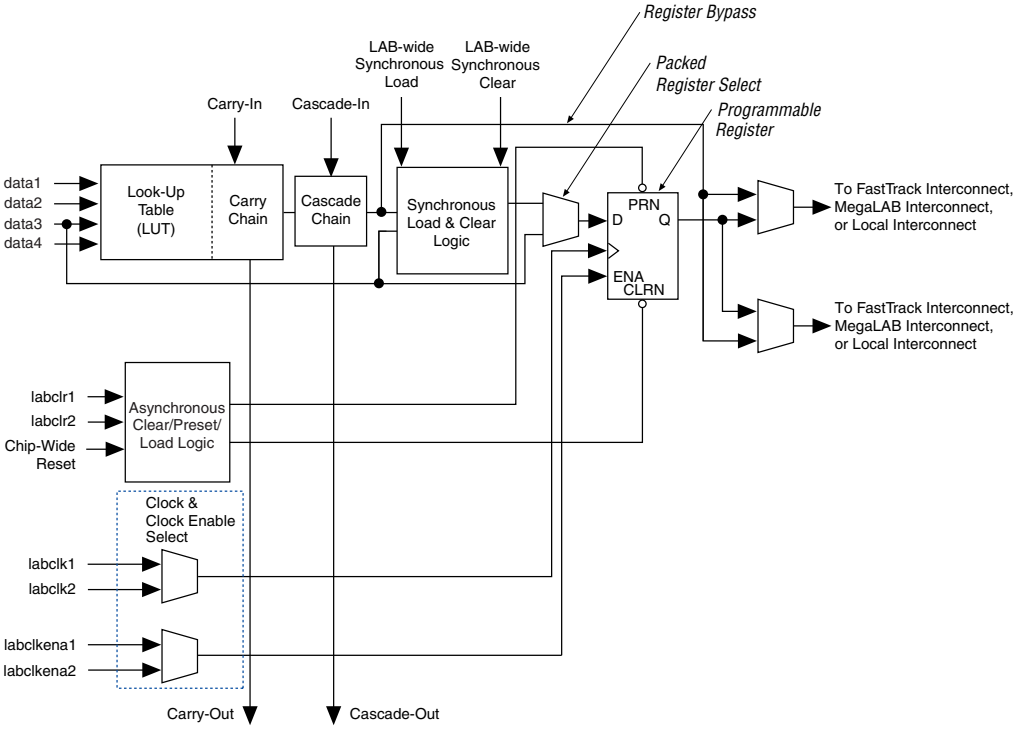
(2) The `LABCLR1` and `LABCLR2` signals also control asynchronous load and asynchronous preset for LEs within the LAB.

(3) The `SYNCCLR` signal can be generated by the local interconnect or global signals.

Logic Element

The LE, the smallest unit of logic in the APEX 20K architecture, is compact and provides efficient logic usage. Each LE contains a four-input LUT, which is a function generator that can quickly implement any function of four variables. In addition, each LE contains a programmable register and carry and cascade chains. Each LE drives the local interconnect, MegaLAB interconnect, and FastTrack Interconnect routing structures. See Figure 5.

Figure 5. APEX 20K Logic Element



Each LE's programmable register can be configured for D, T, JK, or SR operation. The register's clock and clear control signals can be driven by global signals, general-purpose I/O pins, or any internal logic. For combinatorial functions, the register is bypassed and the output of the LUT drives the outputs of the LE.

Figure 10. FastTrack Connection to Local Interconnect

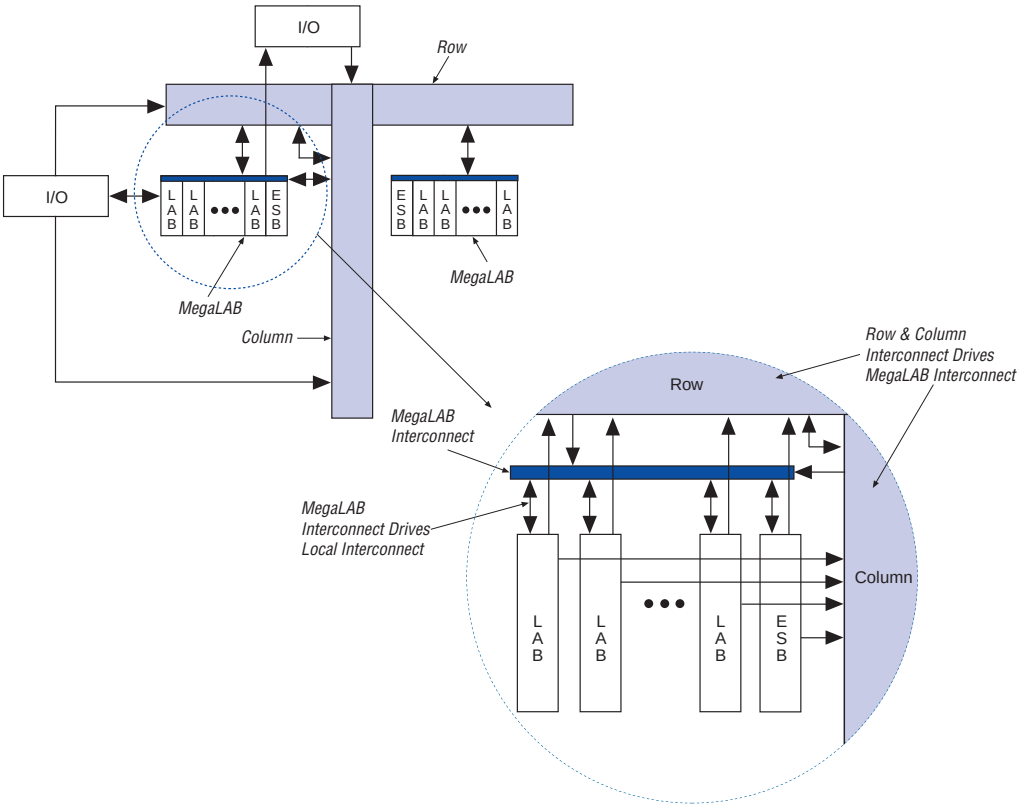


Figure 12. APEX 20KE FastRow Interconnect

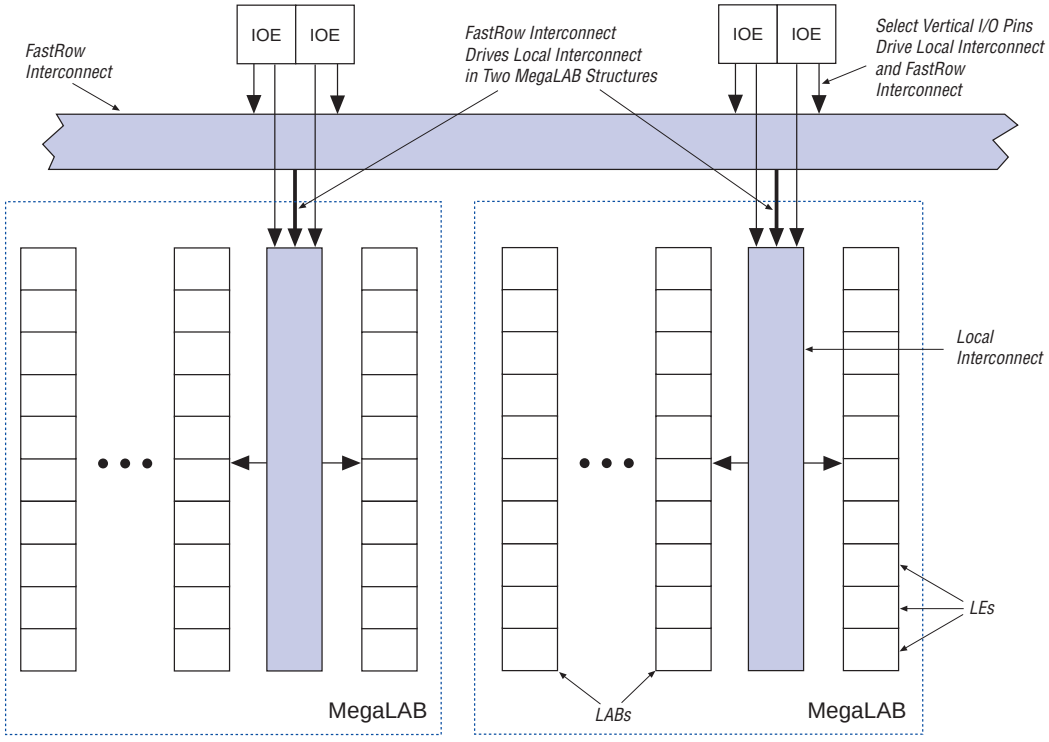


Table 9 summarizes how various elements of the APEX 20K architecture drive each other.

Table 9. APEX 20K Routing Scheme

Source	Destination								
	Row I/O Pin	Column I/O Pin	LE	ESB	Local Interconnect	MegaLAB Interconnect	Row FastTrack Interconnect	Column FastTrack Interconnect	FastRow Interconnect
Row I/O Pin					✓	✓	✓	✓	
Column I/O Pin								✓	✓ (1)
LE					✓	✓	✓	✓	
ESB					✓	✓	✓	✓	
Local Interconnect	✓	✓	✓	✓					
MegaLAB Interconnect					✓				
Row FastTrack Interconnect						✓		✓	
Column FastTrack Interconnect						✓	✓		
FastRow Interconnect					✓ (1)				

Note to Table 9:
(1) This connection is supported in APEX 20KE devices only.

Product-Term Logic

The product-term portion of the MultiCore architecture is implemented with the ESB. The ESB can be configured to act as a block of macrocells on an ESB-by-ESB basis. Each ESB is fed by 32 inputs from the adjacent local interconnect; therefore, it can be driven by the MegaLAB interconnect or the adjacent LAB. Also, nine ESB macrocells feed back into the ESB through the local interconnect for higher performance. Dedicated clock pins, global signals, and additional inputs from the local interconnect drive the ESB control signals.

In product-term mode, each ESB contains 16 macrocells. Each macrocell consists of two product terms and a programmable register. Figure 13 shows the ESB in product-term mode.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

APEX 20K ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20K device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

The APEX 20K IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times, or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The Quartus II software Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20K IOE offers one output enable per pin, the Quartus II software Compiler can emulate open-drain operation efficiently.

The APEX 20K IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

APEX 20KE devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KE IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KE IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II software compiler can set these delays automatically to minimize setup time while providing a zero hold time.

Table 11 describes the APEX 20KE programmable delays and their logic options in the Quartus II software.

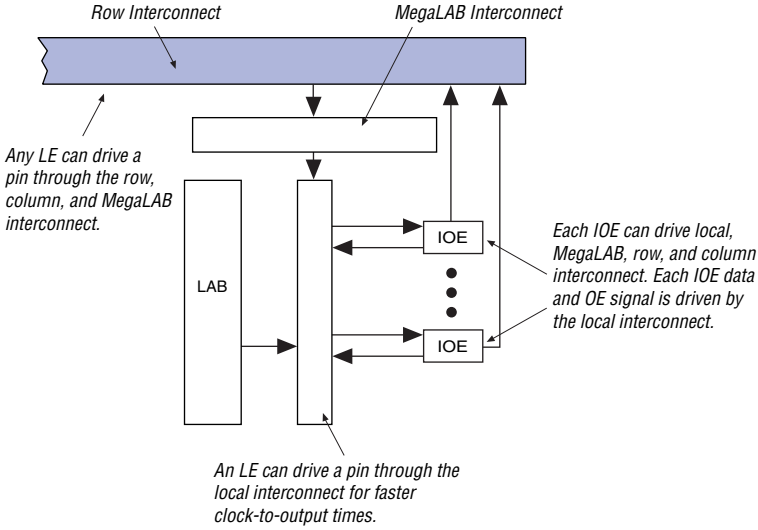
Table 11. APEX 20KE Programmable Delay Chains

Programmable Delays	Quartus II Logic Option
Input Pin to Core Delay	Decrease input delay to internal cells
Input Pin to Input Register Delay	Decrease input delay to input registers
Core to Output Register Delay	Decrease input delay to output register
Output Register t_{CO} Delay	Increase delay to output pin
Clock Enable Delay	Increase clock enable delay

The register in the APEX 20KE IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. Figure 26 shows how fast bidirectional I/O pins are implemented in APEX 20KE devices. This feature is useful for cases where the APEX 20KE device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 27 shows how a row IOE connects to the interconnect.

Figure 27. Row IOE Connection to the Interconnect



Under hot socketing conditions, APEX 20KE devices will not sustain any damage, but the I/O pins will drive out.

MultiVolt I/O Interface

The APEX device architecture supports the MultiVolt I/O interface feature, which allows APEX devices in all packages to interface with systems of different supply voltages. The devices have one set of VCC pins for internal operation and input buffers (VCCINT), and another set for I/O output drivers (VCCIO).

The APEX 20K VCCINT pins must always be connected to a 2.5 V power supply. With a 2.5-V V_{CCINT} level, input pins are 2.5-V, 3.3-V, and 5.0-V tolerant. The VCCIO pins can be connected to either a 2.5-V or 3.3-V power supply, depending on the output requirements. When VCCIO pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When the VCCIO pins are connected to a 3.3-V power supply, the output high is 3.3 V and is compatible with 3.3-V or 5.0-V systems.

Table 12 summarizes 5.0-V tolerant APEX 20K MultiVolt I/O support.

Table 12. 5.0-V Tolerant APEX 20K MultiVolt I/O Support

V_{CCIO} (V)	Input Signals (V)			Output Signals (V)		
	2.5	3.3	5.0	2.5	3.3	5.0
2.5	✓	✓(1)	✓(1)	✓		
3.3	✓	✓	✓(1)	✓(2)	✓	✓

Notes to Table 12:

(1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}.

(2) When V_{CCIO} = 3.3 V, an APEX 20K device can drive a 2.5-V device with 3.3-V tolerant inputs.

Open-drain output pins on 5.0-V tolerant APEX 20K devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

Figure 39. ESB Synchronous Timing Waveforms

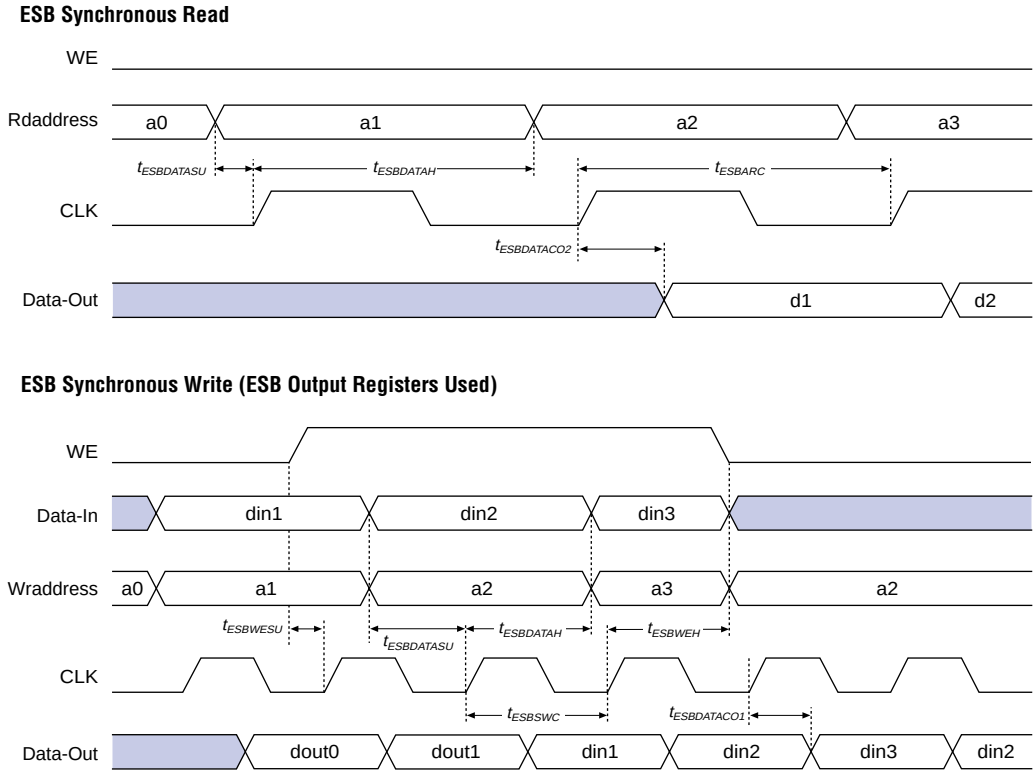


Figure 40 shows the timing model for bidirectional I/O pin timing.

Notes to Tables 43 through 48:
(1) This parameter is measured without using ClockLock or ClockBoost circuits.
(2) This parameter is measured using ClockLock or ClockBoost circuits.

Tables 49 through 54 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K30E APEX 20KE devices.

Table 49. EP20K30E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.02		0.02		ns
t_{H}	0.11		0.16		0.23		ns
t_{CO}		0.32		0.45		0.67	ns
t_{LUT}		0.85		1.20		1.77	ns

Table 60. EP20K60E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.77		2.91		3.11		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	4.84	2.00	5.31	2.00	5.81	ns
$t_{XZBIDIR}$		6.47		7.44		8.65	ns
$t_{ZXBIDIR}$		6.47		7.44		8.65	ns
$t_{INSUBIDIRPLL}$	3.44		3.24		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	3.37	0.50	3.69	-	-	ns
$t_{XZBIDIRPLL}$		5.00		5.82		-	ns
$t_{ZXBIDIRPLL}$		5.00		5.82		-	ns

Tables 61 through 66 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K100E APEX 20KE devices.

Table 61. EP20K100E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.25		0.25		0.25		ns
t_{H}	0.25		0.25		0.25		ns
t_{CO}		0.28		0.28		0.34	ns
t_{LUT}		0.80		0.95		1.13	ns

Table 62. EP20K100E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.61		1.84		1.97	ns
t_{ESBSRC}		2.57		2.97		3.20	ns
t_{ESBAWC}		0.52		4.09		4.39	ns
t_{ESBSWC}		3.17		3.78		4.09	ns
$t_{ESBWASU}$	0.56		6.41		0.63		ns
t_{ESBWAH}	0.48		0.54		0.55		ns
$t_{ESBWDSU}$	0.71		0.80		0.81		ns
t_{ESBWDH}	.048		0.54		0.55		ns
$t_{ESBRASU}$	1.57		1.75		1.87		ns
t_{ESBRAH}	0.00		0.00		0.20		ns
$t_{ESBWESU}$	1.54		1.72		1.80		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.16		-0.20		-0.20		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.12		0.08		0.13		ns
$t_{ESBRADDRSU}$	0.17		0.15		0.19		ns
$t_{ESBDATACO1}$		1.20		1.39		1.52	ns
$t_{ESBDATACO2}$		2.54		2.99		3.22	ns
t_{ESBDD}		3.06		3.56		3.85	ns
t_{PD}		1.73		2.02		2.20	ns
$t_{PTERMSU}$	1.11		1.26		1.38		ns
$t_{PTERMCO}$		1.19		1.40		1.08	ns

Table 63. EP20K100E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.24		0.27		0.29	ns
t_{F5-20}		1.04		1.26		1.52	ns
t_{F20+}		1.12		1.36		1.86	ns

Table 69. EP20K160E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.26		0.28	ns
t_{F5-20}		1.00		1.18		1.35	ns
t_{F20+}		1.95		2.19		2.30	ns

Table 70. EP20K160E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.34		1.43		1.55		ns
t_{CL}	1.34		1.43		1.55		ns
t_{CLRP}	0.18		0.19		0.21		ns
t_{PREP}	0.18		0.19		0.21		ns
t_{ESBCH}	1.34		1.43		1.55		ns
t_{ESBCL}	1.34		1.43		1.55		ns
t_{ESBWP}	1.15		1.45		1.73		ns
t_{ESBRP}	0.93		1.15		1.38		ns

Table 71. EP20K160E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.23		2.34		2.47		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.07	2.00	5.59	2.00	6.13	ns
$t_{INSUPLL}$	2.12		2.07		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	3.00	0.50	3.35	-	-	ns

Table 76. EP20K200E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.44		2.65		ns
t_{CL}	1.36		2.44		2.65		ns
t_{CLRP}	0.18		0.19		0.21		ns
t_{PREP}	0.18		0.19		0.21		ns
t_{ESBCH}	1.36		2.44		2.65		ns
t_{ESBCL}	1.36		2.44		2.65		ns
t_{ESBWP}	1.18		1.48		1.76		ns
t_{ESBRP}	0.95		1.17		1.41		ns

Table 77. EP20K200E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.24		2.35		2.47		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.12	2.00	5.62	2.00	6.11	ns
$t_{INSUPLL}$	2.13		2.07		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	3.01	0.50	3.36	-	-	ns

Table 86. EP20K400E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.67		1.91		1.99	ns
t_{ESBSRC}		2.30		2.66		2.93	ns
t_{ESBAWC}		3.09		3.58		3.99	ns
t_{ESBSWC}		3.01		3.65		4.05	ns
$t_{ESBWASU}$	0.54		0.63		0.65		ns
t_{ESBWAH}	0.36		0.43		0.42		ns
$t_{ESBWDSU}$	0.69		0.77		0.84		ns
t_{ESBWDH}	0.36		0.43		0.42		ns
$t_{ESBRASU}$	1.61		1.77		1.86		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.35		1.47		1.61		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.18		-0.30		-0.27		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	-0.02		-0.11		-0.03		ns
$t_{ESBRADDRSU}$	0.06		-0.01		-0.05		ns
$t_{ESBDATACO1}$		1.16		1.40		1.54	ns
$t_{ESBDATACO2}$		2.18		2.55		2.85	ns
t_{ESBDD}		2.73		3.17		3.58	ns
t_{PD}		1.57		1.83		2.07	ns
$t_{PTERMSU}$	0.92		0.99		1.18		ns
$t_{PTERMCO}$		1.18		1.43		1.17	ns

Table 94. EP20K600E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	2.00		2.50		2.75		ns
t_{CL}	2.00		2.50		2.75		ns
t_{CLRP}	0.18		0.26		0.34		ns
t_{PREP}	0.18		0.26		0.34		ns
t_{ESBCH}	2.00		2.50		2.75		ns
t_{ESBCL}	2.00		2.50		2.75		ns
t_{ESBWP}	1.17		1.68		2.18		ns
t_{ESBRP}	0.95		1.35		1.76		ns

Table 95. EP20K600E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.74		2.74		2.87		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.51	2.00	6.06	2.00	6.61	ns
$t_{INSUPLL}$	1.86		1.96		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.62	0.50	2.91	-	-	ns

Table 96. EP20K600E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	0.64		0.98		1.08		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.51	2.00	6.06	2.00	6.61	ns
$t_{XZBIDIR}$		6.10		6.74		7.10	ns
$t_{ZXBIDIR}$		6.10		6.74		7.10	ns
$t_{INSUBIDIRPLL}$	2.26		2.68		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.62	0.50	2.91	-	-	ns
$t_{XZBIDIRPLL}$		3.21		3.59		-	ns
$t_{ZXBIDIRPLL}$		3.21		3.59		-	ns

Table 108. EP20K1500E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	3.47		3.68		3.99		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	6.18	2.00	6.81	2.00	7.36	ns
$t_{XZBIDIR}$		6.91		7.62		8.38	ns
$t_{ZXBIDIR}$		6.91		7.62		8.38	ns
$t_{INSUBIDIRPLL}$	3.05		3.26				ns
$t_{INHBIDIRPLL}$	0.00		0.00				ns
$t_{OUTCOBIDIRPLL}$	0.50	2.67	0.50	2.99			ns
$t_{XZBIDIRPLL}$		3.41		3.80			ns
$t_{ZXBIDIRPLL}$		3.41		3.80			ns

Tables 109 and 110 show selectable I/O standard input and output delays for APEX 20KE devices. If you select an I/O standard input or output delay other than LVCMOS, add or subtract the selected speed grade to or from the LVCMOS value.

Table 109. Selectable I/O Standard Input Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.04		0.05	ns
1.8 V		–0.11		0.03		0.04	ns
PCI		0.01		0.09		0.10	ns
GTL+		–0.24		–0.23		–0.19	ns
SSTL-3 Class I		–0.32		–0.21		–0.47	ns
SSTL-3 Class II		–0.08		0.03		–0.23	ns
SSTL-2 Class I		–0.17		–0.06		–0.32	ns
SSTL-2 Class II		–0.16		–0.05		–0.31	ns
LVDS		–0.12		–0.12		–0.12	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns